FDD6030L



SEMICONDUCTOR

FDD6030L N-Channel Logic Level Enhancement Mode Field Effect Transistor

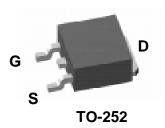
General Description

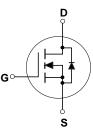
These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications such as DC/DC converters and high efficiency switching circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

• 50 A, 30 V. $R_{DS(ON)} = 0.0135 \Omega @ V_{GS} = 10 V$ $R_{DS(ON)} = 0.0200 \Omega @ V_{GS} = 4.5 V.$

- Low gate charge.
- Fast switching speed.
- Low Crss.





Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 20	V
ID	Maximum Drain Current -Continuous	(Note 1)	50	A
		(Note 1a)	12	
	Maximum Drain Current -Pulsed		150	
PD	Maximum Power Dissipation @ $T_c = 25^{\circ}C$ ((Note 1)	60	W
	$T_A = 25^{\circ}C$	(Note 1a)	3.2	
	$T_A = 25^{\circ}C$	(Note 1b)	1.3	
T _J , T _{stg}	Operating and Storage Junction Temperature R	ange	-55 to +150	۰C

Thermal Characteristics

R _{θJC}	Thermal Resistance, Junction-to- Case	(Note 1)	2.1	∘C/W
R _{θJA}	Thermal Resistance, Junction-to- Ambient	(Note 1a)	39	∘C/W
		(Note 1b)	96	°C/W

Package Marking and Ordering Information

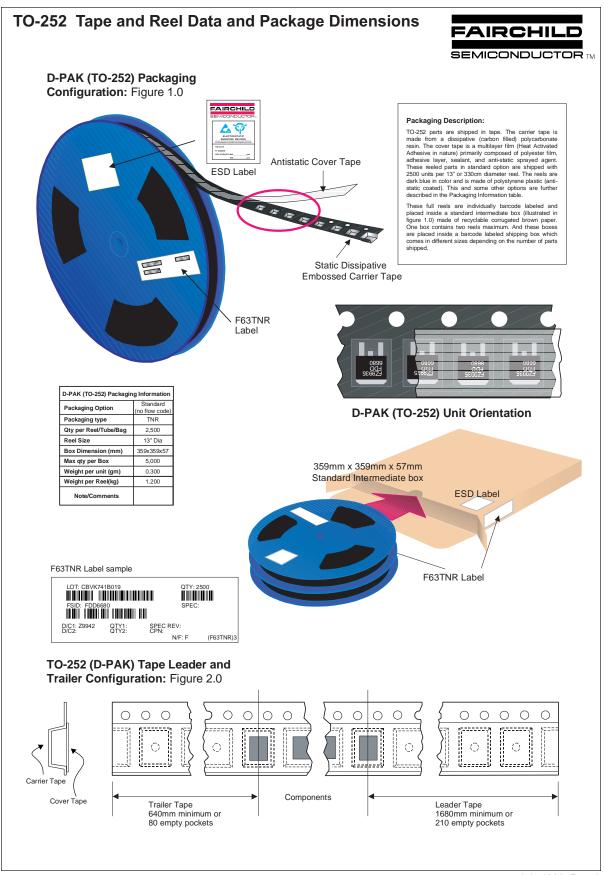
Device Marking	Device	Reel Size	Tape width	Quantity
FDD6030L	FDD6030L	13"	16mm	2500

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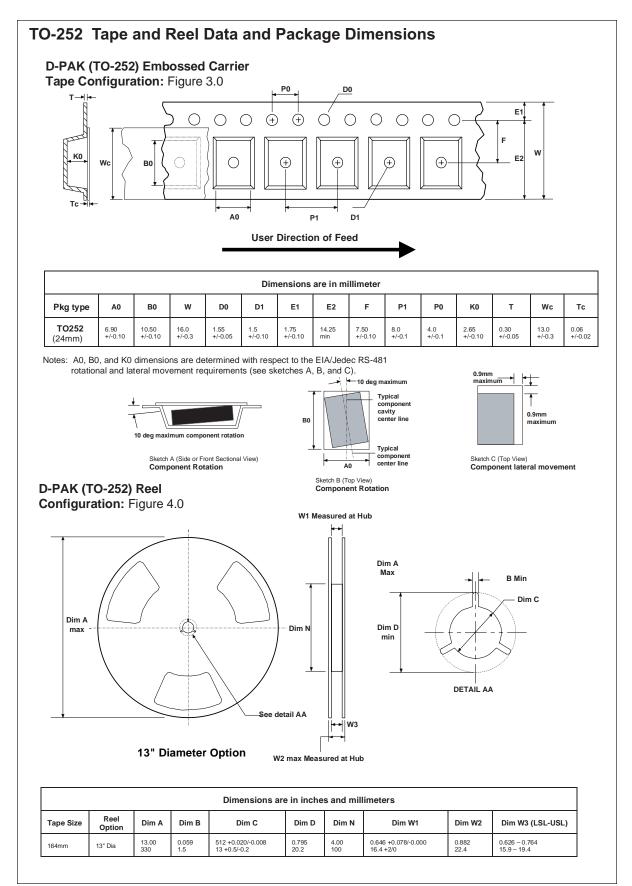
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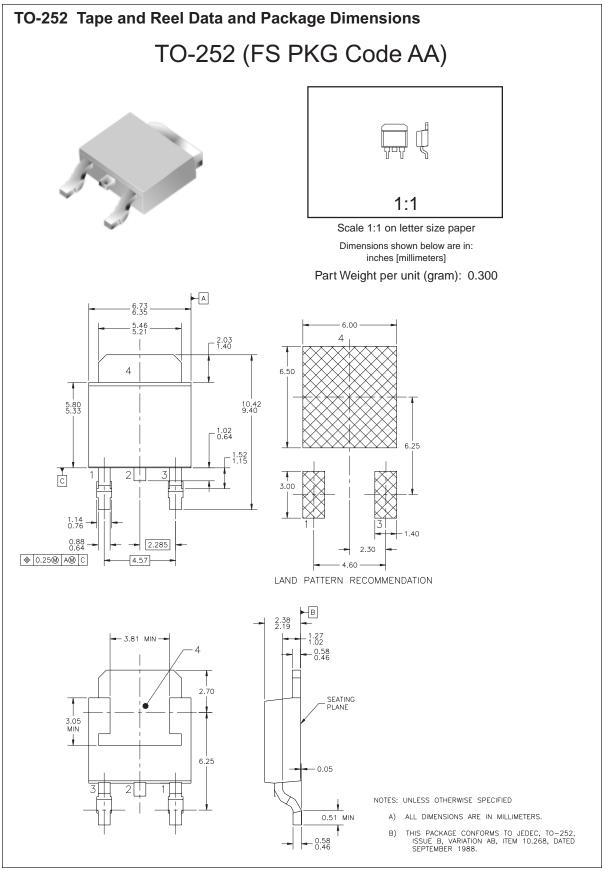
FDD6030L Rev. A1

FDD6030L



July 1999, Rev. A





September 1999, Rev. A

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